N-Channel 20-V (D-S) MOSFET with Trench Schottky Diode

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a]	Q_g (Typ.)
20	0.225 at V_{GS} = 4.5 V	1.5	1.1 nC
	0.270 at V_{GS} = 2.5 V	1.5	
	0.345 at V_{GS} = 1.8 V	1.5	
	0.960 at V_{GS} = 1.5 V	0.5	

SCHOTTKY PRODUCT SUMMARY		
V_{KA} (V)	V_f (V) Diode Forward Voltage	I_F (A)[a]
30	0.29 at 10 mA	0.4

FEATURES

- **Halogen-free According to IEC 61249-2-21**
- LITTLE FOOT® *Plus* Schottky Power MOSFET
- New Thermally Enhanced PowerPAK® SC-75 Package
  - Small Footprint Area
  - Low On-Resistance
  - Thin 0.75 mm profile
- Typical ESD Protection 2800 V

Pb-free

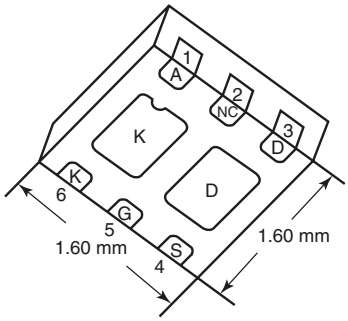
RoHS COMPLIANT

HALOGEN FREE

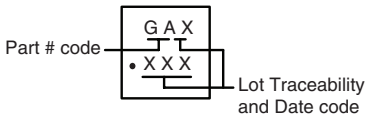
APPLICATIONS

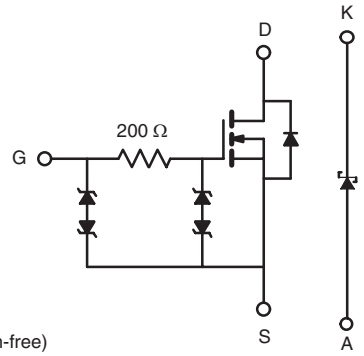
- Portable Devices
- DC/DC Converters

PowerPAK SC75-6L-Dual



Marking Code





Ordering Information: SiB800EDK-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage (MOSFET)		V_{DS}	20	V
Reverse Voltage (Schottky)		V_{KA}	30	
Gate-Source Voltage (MOSFET)		V_{GS}	± 6	
Continuous Drain Current (T_J = 150 °C) (MOSFET)	T_C = 25 °C	I_D	1.5[a]	A
	T_C = 70 °C		1.5[a]	
	T_A = 25 °C		1.5[a, b, c]	
	T_A = 70 °C		1.3[b, c]	
Pulsed Drain Current (MOSFET)		I_{DM}	4	
Continuous Source-Drain Diode Current (MOSFET Diode Conduction)	T_C = 25 °C	I_S	1.5[a]	
	T_A = 25 °C		0.9[b, c]	
Average Forward Current (Schottky)		I_F	0.4[b]	
Pulsed Forward Current (Schottky)		I_{FM}	0.8	
Maximum Power Dissipation (MOSFET)	T_C = 25 °C	P_D	3.1	W
	T_C = 70 °C		2	
	T_A = 25 °C		1.1[b, c]	
	T_A = 70 °C		0.7[b, c]	
Maximum Power Dissipation (Schottky)	T_C = 25 °C		3.1	
	T_C = 70 °C		2	
	T_A = 25 °C		1.1[b, c]	
	T_A = 70 °C		0.7[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)[d, e]			260	

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (MOSFET)[b, f]	t ≤ 5 s	R_{thJA}	90	115	°C/W
Maximum Junction-to-Case (Drain) (MOSFET)	Steady State	R_{thJC}	32	40	
Maximum Junction-to-Ambient (Schottky)[b, f]	t ≤ 5 s	R_{thJA}	90	115	
Maximum Junction-to-Case (Drain) (Schottky)	Steady State	R_{thJC}	32	40	

Notes:
a. Package limited.
b. Surface Mounted on 1" x 1" FR4 board.
c. t = 5 s.
d. See Solder Profile (*www.vishay.com/ppg?73257*). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
f. Maximum under Steady State conditions is 125 °C/W.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted

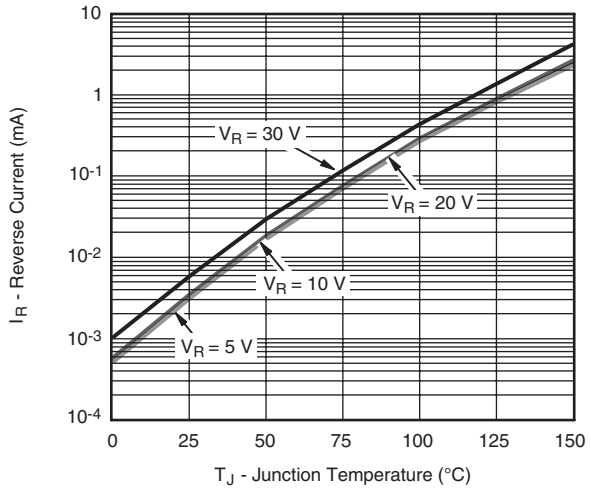
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		21		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 2.3		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	0.4		1.0	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 3 V			± 1	µA
		V_{DS} = 0 V, V_{GS} = ± 6 V			± 1	mA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V			1	µA
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 4.5 V	4			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 1.6 A		0.183	0.225	Ω
		V_{GS} = 2.5 V, I_D = 1.5 A		0.220	0.270	
		V_{GS} = 1.8 V, I_D = 1.3 A		0.275	0.345	
		V_{GS} = 1.5 V, I_D = 0.3 A		0.320	0.960	
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 1.6 A		3.5		S
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 1.7 A		1.1	1.7	nC
Gate-Source Charge	Q_{gs}			0.2		
Gate-Drain Charge	Q_{gd}			0.1		
Gate Resistance	R_g	f = 1 MHz		200		Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 10 V, R_L = 7.7 Ω I_D ≅ 1.3 A, V_{GEN} = 4.5 V, R_g = 1 Ω		20	30	ns
Rise Time	t_r			12	20	
Turn-Off DelayTime	$t_{d(off)}$			70	105	
Fall Time	t_f			20	30	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			1.5	A
Pulse Diode Forward Current	I_{SM}				4	
Body Diode Voltage	V_{SD}	I_S = 1.3 A, V_{GS} = 0 V		0.9	1.2	V

Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

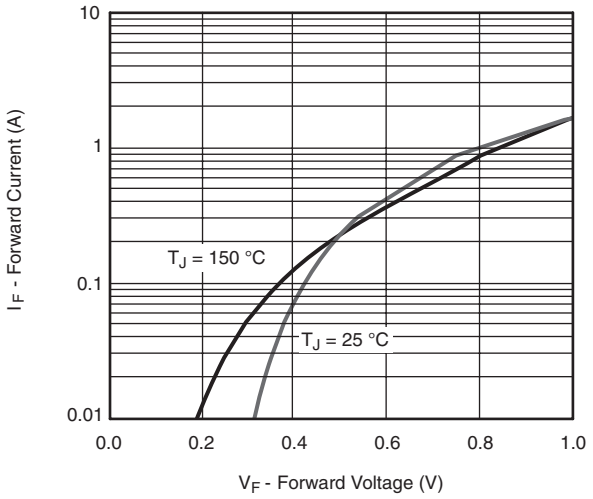
SCHOTTKY SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Forward Voltage Drop	V_F	I_F = 10 mA		0.23	0.29	V
		I_F = 10 mA, T_J = 125 °C		0.11	0.14	
		I_F = 0.1 A		0.32	0.38	
Maximum Reverse Leakage Current	I_{rm}	V_r = 20 V		0.005	0.050	mA
		V_r = 20 V, T_J = 85 °C		0.150	1.5	
Junction Capacitance	C_T	V_r = 15 V		16		pF

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

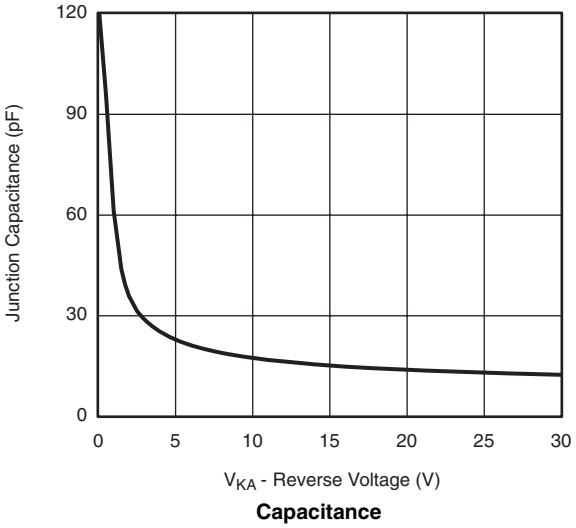
SCHOTTKY TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



Reverse Current vs. Junction Temperature

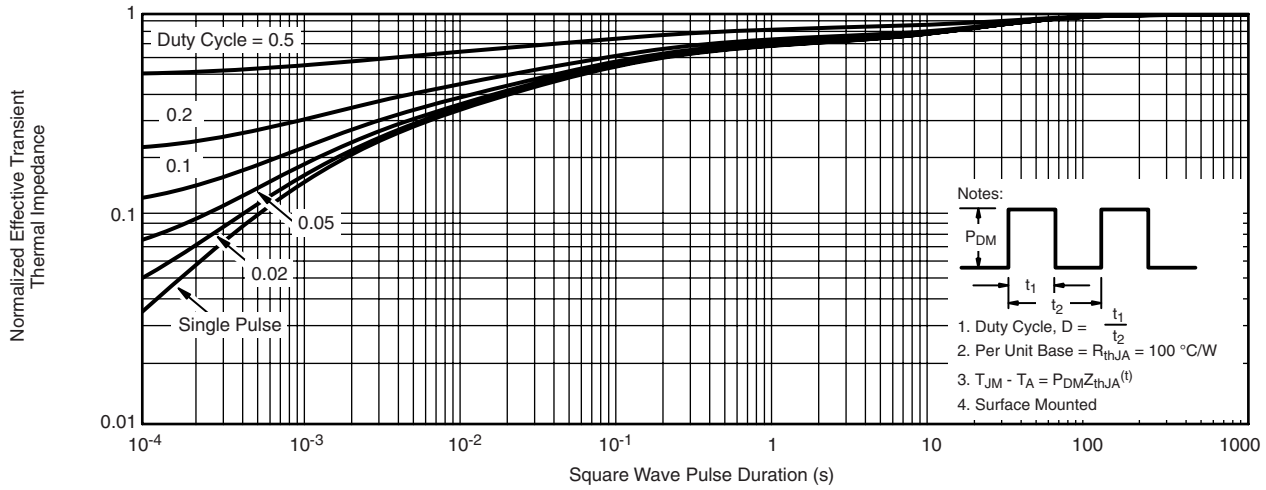


Forward Voltage Drop

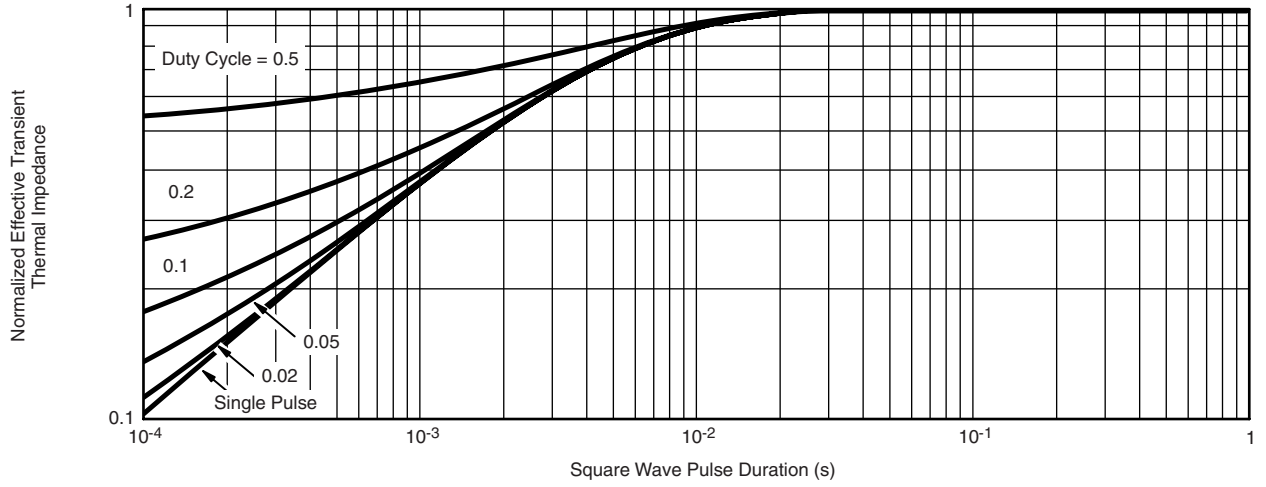


Capacitance

SCHOTTKY TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted

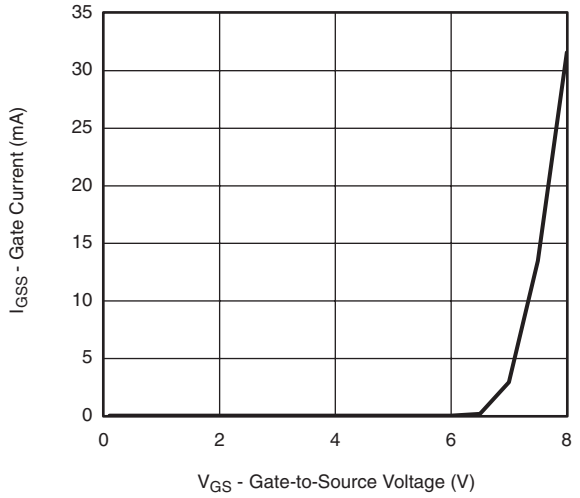


Normalized Thermal Transient Impedance, Junction-to-Ambient

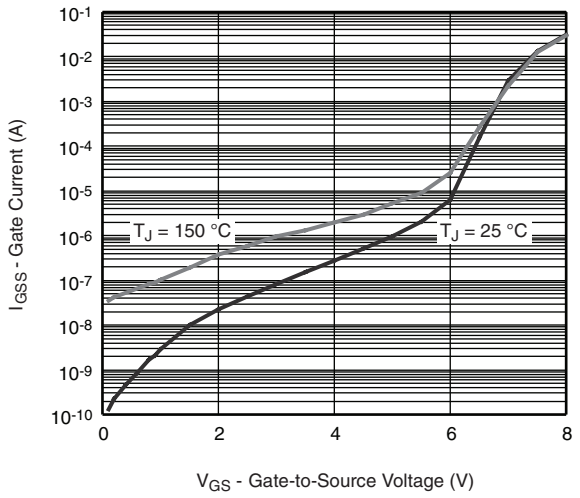


Normalized Thermal Transient Impedance, Junction-to-Case

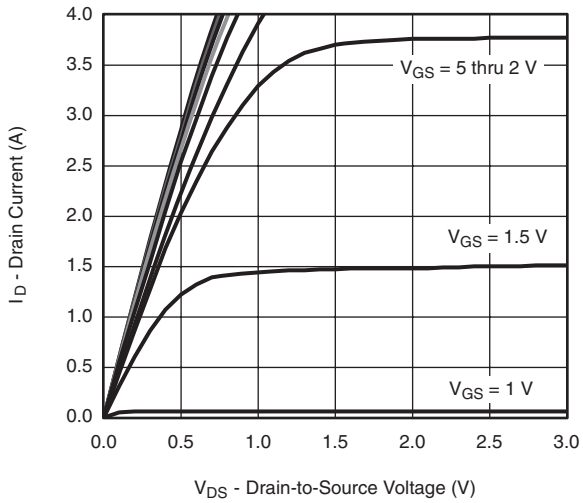
MOSFET TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



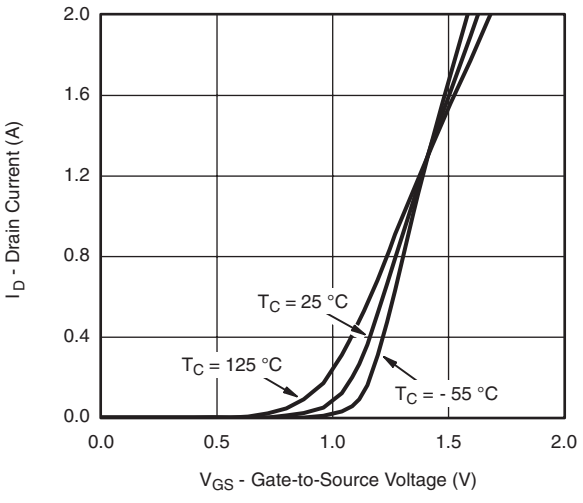
Gate Current vs. Gate-to-Source Voltage



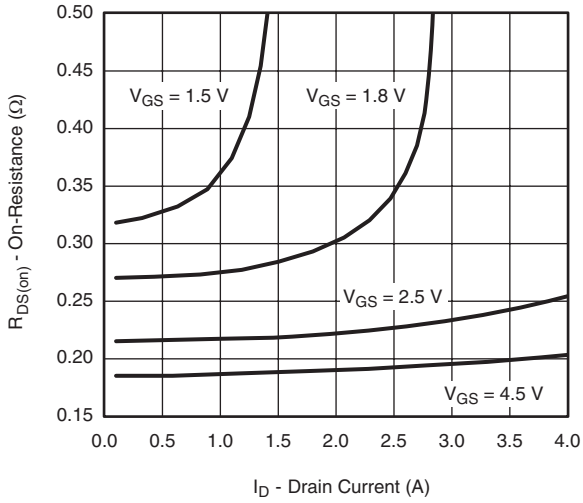
Gate Current vs. Gate-to-Source Voltage



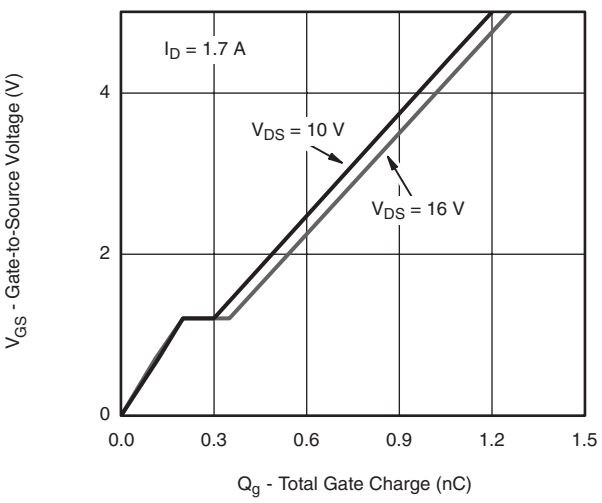
Output Characteristics



Transfer Characteristics

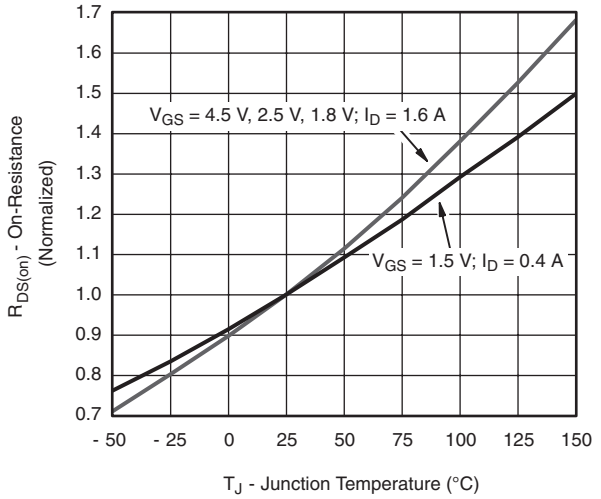


On-Resistance vs. Drain Current

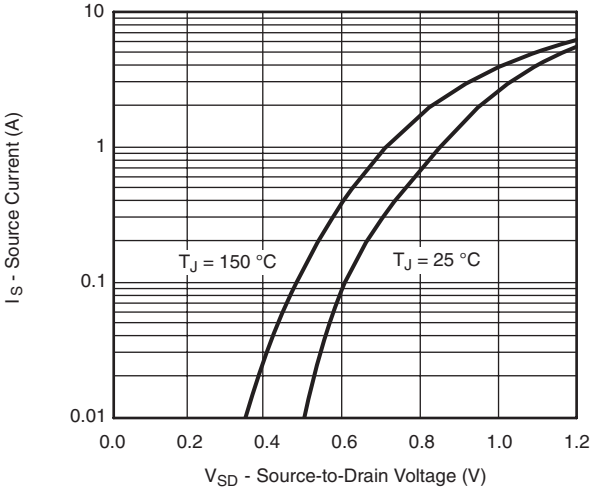


Gate Charge

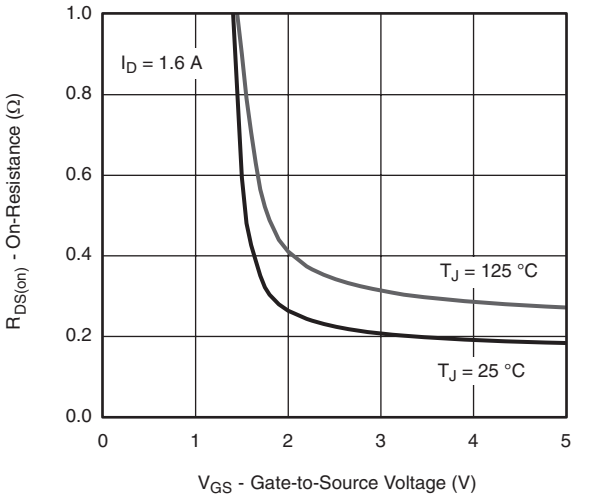
MOSFET TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



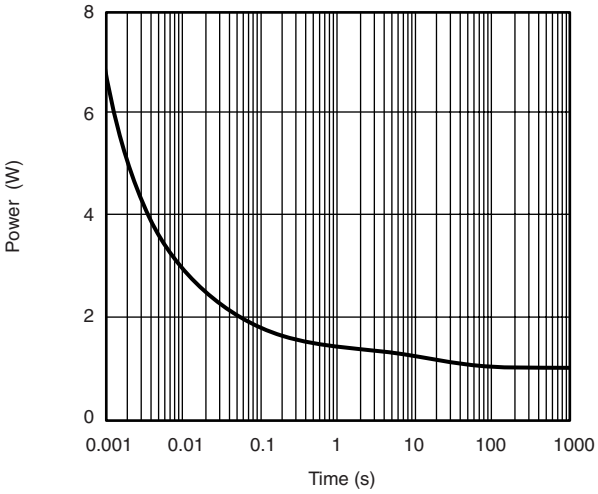
Normalized On-Resistance vs. Junction Temperature



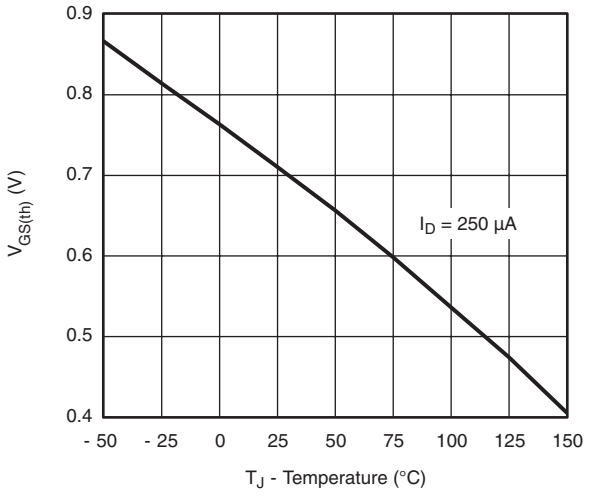
Source-Drain Diode Forward Voltage



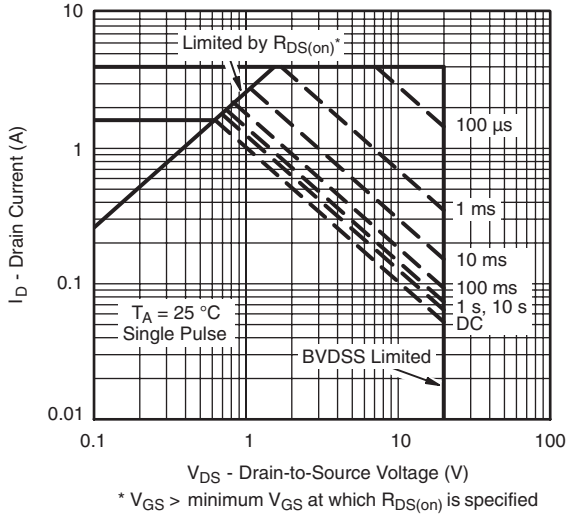
On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



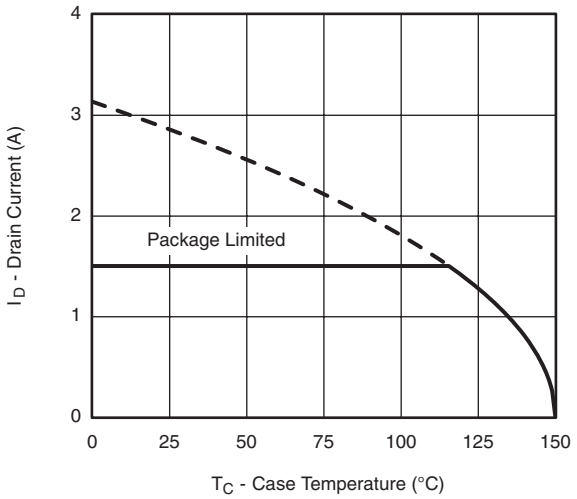
Threshold Voltage



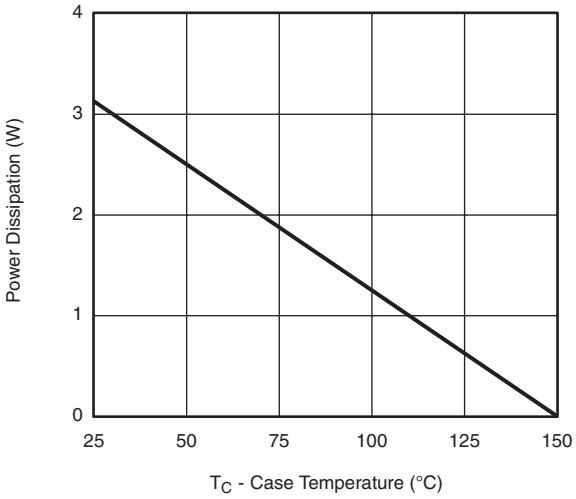
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

MOSFET TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



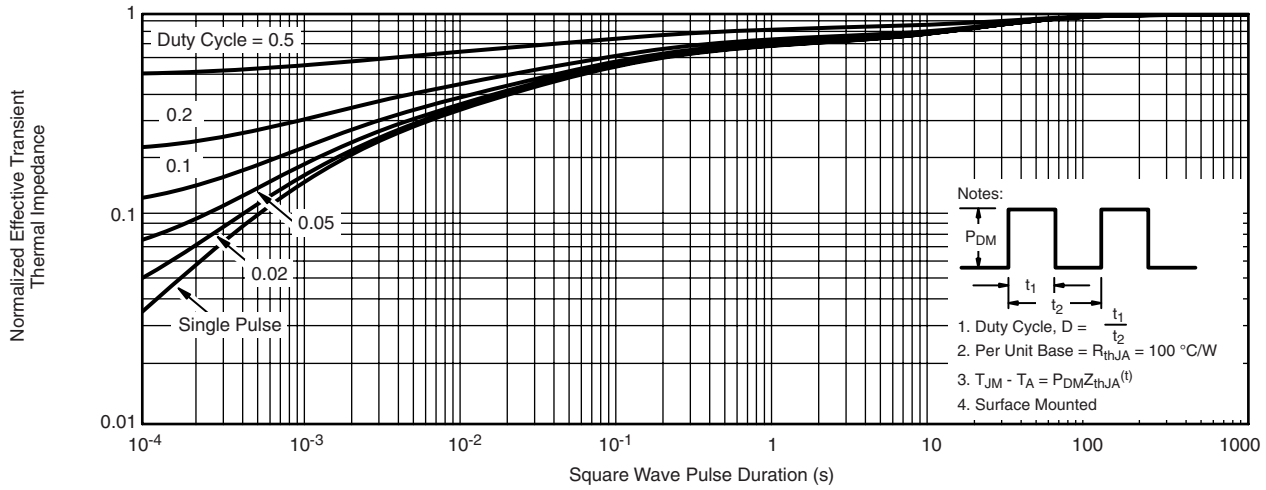
Current Derating*



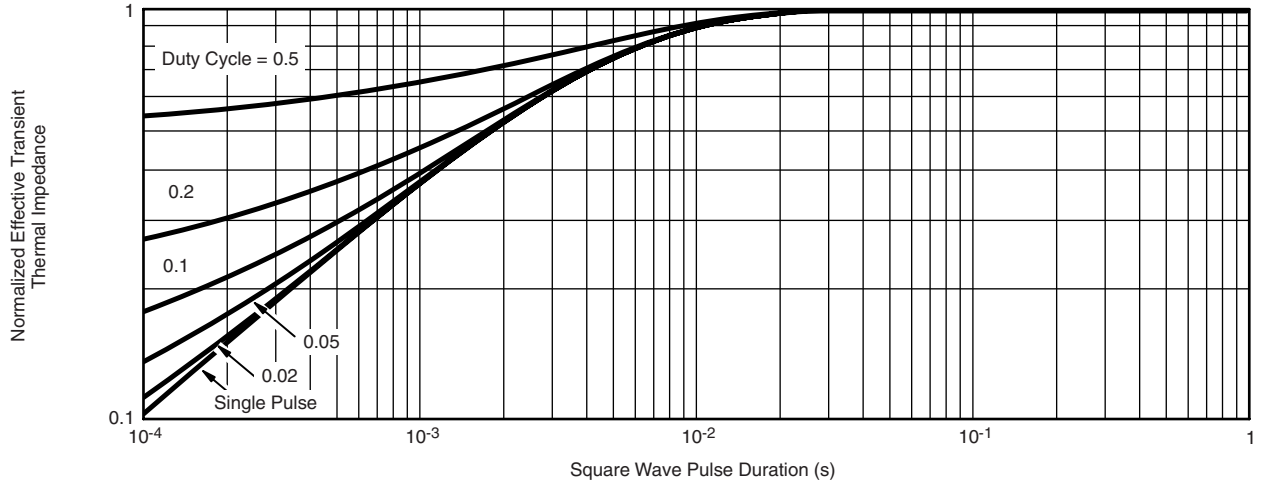
Power Derating

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

MOSFET TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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